

APPLICATION NO. 09/756846

August 9, 2004

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CLMPTO

1. (Previously Presented) A semiconductor device comprising:

a thick film wiring having a first film thickness;

a thin film wiring having a second film thickness that is smaller than the first film thickness, said thick film wiring and said thin film wiring being formed in a single layer; and

a hard mask covering only the surface of said thick film therewith;

wherein said hard mask is resistant to etching adapted for patterning of said thick film wiring and also to etching adapted for patterning of said thin film wiring, while being resistant to heat.

2. (Original) The semiconductor device according to Claim 1, wherein said hard mask comprises a silicon oxide film.

3. (Original) The semiconductor device according to Claim 1, wherein said hard mask comprises a silicon nitride film.

4. (Original) The semiconductor device according to Claim 1, wherein said hard mask comprises a tungsten film.

5. (Currently Amended) The [[A]] semiconductor device according to Claim 1 comprising:

a thick-film wiring having a first film thickness;

a thin-film wiring having a second film thickness that is smaller than the first film thickness, said thick-film wiring and said thin-film wiring being formed in a single layer; and

a hard mask covering the surface of said thick-film therewith;

wherein said hard mask is resistant to etching adapted for patterning of said thick-film wiring and also to etching adapted for patterning of said thin-film wiring, while being resistant to heat, wherein

said thick film wiring serves as a wiring for an electric supply of said semiconductor device or as a wiring for ground.

CLAIMS 6-16 (CANCELLED)

17. (Currently Amended) [[A]] The semiconductor device according to claim 1, wherein the hard mask is resistant to heat at 400°C.